

# Silicon Carbide (SiC) Module – EliteSiC, 40 mΩ SiC M1 MOSFET, 1200 V + 40 A, 1200 V SiC Diode, Three Channel Full SiC Boost, Q1 Package

## Product Preview

## NXH40B120MNQ1SNG

The NXH40B120MNQ1SNG is a power module containing a three channel boost stage. The integrated SiC MOSFETs and SiC Diodes provide lower conduction losses and switching losses, enabling designers to achieve high efficiency and superior reliability.

### Features

- 1200 V 40 mΩ SiC MOSFETs
- Low Reverse Recovery and Fast Switching SiC Diodes
- 1200 V Bypass and Anti-parallel Diodes
- Low Inductive Layout
- Solderable Pins
- Thermistor
- This Device is Pb-Free, Halogen Free/BFR Free and is RoHS Compliant

### Typical Applications

- Solar Inverters
- Uninterruptable Power Supplies

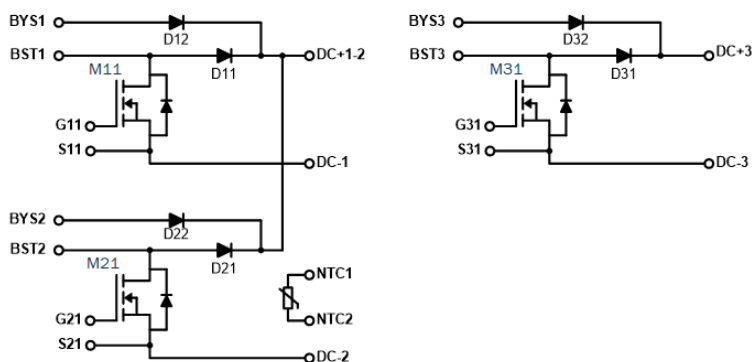
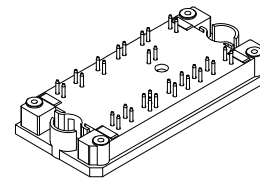


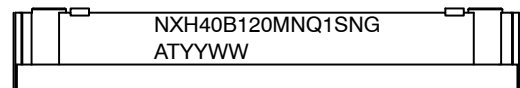
Figure 1. NXH80B120MNQ0SNG Schematic Diagram

This document contains information on a product under development. onsemi reserves the right to change or discontinue this product without notice.



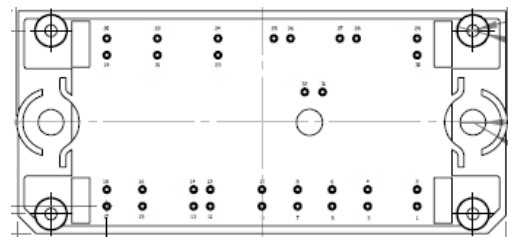
PIM32, 71x37.4  
(SOLDER PIN)  
CASE 180BQ

### MARKING DIAGRAM



NXH40B120MNQ1SNG = Device Code  
G = Pb-Free Package  
AT = Assembly & Test Site Code  
YYWW = Year and Work Week Code

### PIN CONNECTIONS



### ORDERING INFORMATION

See detailed ordering and shipping information on page 4 of this data sheet.

# NXH40B120MNQ1SNG

## ABSOLUTE MAXIMUM RATINGS (Note 1) $T_J = 25^{\circ}\text{C}$ unless otherwise noted

| Rating                                                                            | Symbol         | Value   | Unit               |
|-----------------------------------------------------------------------------------|----------------|---------|--------------------|
| <b>BOOST SiC MOSFET (M11, M21, M31)</b>                                           |                |         |                    |
| Drain–Source Voltage                                                              | $V_{DS}$       | 1200    | V                  |
| Gate–Source Voltage                                                               | $V_{GS}$       | –15/+25 | V                  |
| Continuous Drain Current (@ $V_{GS} = 20\text{ V}$ , $T_C = 80^{\circ}\text{C}$ ) | $I_D$          | 44      | A                  |
| Pulsed Drain Current @ $T_C = 80^{\circ}\text{C}$ ( $T_J = 175^{\circ}\text{C}$ ) | $I_{D(Pulse)}$ | 132     | A                  |
| Maximum Power Dissipation @ $T_C = 80^{\circ}\text{C}$                            | $P_{tot}$      | 156     | W                  |
| Minimum Operating Junction Temperature                                            | $T_{JMIN}$     | –40     | $^{\circ}\text{C}$ |
| Maximum Operating Junction Temperature                                            | $T_{JMAX}$     | 175     | $^{\circ}\text{C}$ |

## BOOST DIODE (D11, D21, D31)

|                                                                                        |            |      |                    |
|----------------------------------------------------------------------------------------|------------|------|--------------------|
| Peak Repetitive Reverse Voltage                                                        | $V_{RRM}$  | 1200 | V                  |
| Continuous Forward Current @ $T_C = 80^{\circ}\text{C}$                                | $I_F$      | 53   | A                  |
| Surge Forward Current (60 Hz single half–sine wave)                                    | $I_{FRM}$  | 159  | A                  |
| Maximum Power Dissipation @ $T_C = 80^{\circ}\text{C}$ ( $T_J = 175^{\circ}\text{C}$ ) | $P_{tot}$  | 153  | W                  |
| Minimum Operating Junction Temperature                                                 | $T_{JMIN}$ | –40  | $^{\circ}\text{C}$ |
| Maximum Operating Junction Temperature                                                 | $T_{JMAX}$ | 175  | $^{\circ}\text{C}$ |

## BYPASS DIODE (D12, D22, D32)

|                                                                                               |            |      |                    |
|-----------------------------------------------------------------------------------------------|------------|------|--------------------|
| Peak Repetitive Reverse Voltage                                                               | $V_{RRM}$  | 1200 | V                  |
| Continuous Forward Current @ $T_C = 80^{\circ}\text{C}$ ( $T_J = 150^{\circ}\text{C}$ )       | $I_F$      | 75   | A                  |
| Repetitive Peak Forward Current ( $T_J = 150^{\circ}\text{C}$ , $t_p$ limited by $T_{Jmax}$ ) | $I_{FRM}$  | 225  | A                  |
| Power Dissipation Per Diode @ $T_C = 80^{\circ}\text{C}$ ( $T_J = 150^{\circ}\text{C}$ )      | $P_{tot}$  | 97   | W                  |
| Minimum Operating Junction Temperature                                                        | $T_{JMIN}$ | –40  | $^{\circ}\text{C}$ |
| Maximum Operating Junction Temperature                                                        | $T_{JMAX}$ | 150  | $^{\circ}\text{C}$ |

## THERMAL PROPERTIES

|                           |           |            |                    |
|---------------------------|-----------|------------|--------------------|
| Storage Temperature range | $T_{stg}$ | –40 to 125 | $^{\circ}\text{C}$ |
|---------------------------|-----------|------------|--------------------|

## INSULATION PROPERTIES

|                                                    |          |      |           |
|----------------------------------------------------|----------|------|-----------|
| Isolation test voltage, $t = 1\text{ sec}$ , 60 Hz | $V_{is}$ | 3000 | $V_{RMS}$ |
| Creepage distance                                  |          | 12.7 | mm        |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Refer to [ELECTRICAL CHARACTERISTICS](#), [RECOMMENDED OPERATING RANGES](#) and/or APPLICATION INFORMATION for Safe Operating parameters.

## RECOMMENDED OPERATING RANGES

| Parameter                             | Symbol | Min | Max | Unit               |
|---------------------------------------|--------|-----|-----|--------------------|
| Module Operating Junction Temperature | $T_J$  | –40 | 150 | $^{\circ}\text{C}$ |

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

# NXH40B120MNQ1SNG

## ELECTRICAL CHARACTERISTICS (T<sub>J</sub> = 25°C unless otherwise specified)

| Characteristic                                      | Test Conditions                                                                                                                    | Symbol              | Min | Typ   | Max | Unit |
|-----------------------------------------------------|------------------------------------------------------------------------------------------------------------------------------------|---------------------|-----|-------|-----|------|
| <b>BOOST MOSFET CHARACTERISTICS (M11, M21, M31)</b> |                                                                                                                                    |                     |     |       |     |      |
| Zero Gate Voltage Drain Current                     | V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 1200 V, T <sub>J</sub> = 25°C                                                             | I <sub>DSS</sub>    | –   | –     | 200 | μA   |
| Static Drain-to-Source On Resistance                | V <sub>GS</sub> = 20 V, I <sub>D</sub> = 40 A, T <sub>J</sub> = 25°C                                                               | R <sub>DS(on)</sub> | –   | 40    | 55  | mΩ   |
|                                                     | V <sub>GS</sub> = 20 V, I <sub>D</sub> = 40 A, T <sub>J</sub> = 175°C                                                              |                     | –   | 60    | –   |      |
| Gate-Source Leakage Current                         | V <sub>GS</sub> = 25 V, V <sub>DS</sub> = 0 V                                                                                      | I <sub>GSS</sub>    | –   | –     | 1.0 | μA   |
| Turn-on Delay Time                                  | T <sub>J</sub> = 25°C<br>V <sub>DS</sub> = 700 V, V <sub>GS</sub> = –5 V to 20 V<br>I <sub>D</sub> = 40 A, R <sub>G</sub> = 4.7 Ω  | t <sub>d(on)</sub>  | –   | 17    | –   | ns   |
| Rise Time                                           |                                                                                                                                    | t <sub>r</sub>      | –   | 7.5   | –   |      |
| Turn-off Delay Time                                 |                                                                                                                                    | t <sub>d(off)</sub> | –   | 43.8  | –   |      |
| Fall Time                                           |                                                                                                                                    | t <sub>f</sub>      | –   | 17    | –   |      |
| Turn-on Switching Loss per Pulse                    |                                                                                                                                    | E <sub>on</sub>     | –   | 255   | –   | μJ   |
| Turn-off Switching Loss per Pulse                   |                                                                                                                                    | E <sub>off</sub>    | –   | 125.5 | –   |      |
| Turn-on Delay Time                                  | T <sub>J</sub> = 125°C<br>V <sub>DS</sub> = 700 V, V <sub>GS</sub> = –5 V to 20 V<br>I <sub>D</sub> = 40 A, R <sub>G</sub> = 4.7 Ω | t <sub>d(on)</sub>  | –   | 15.8  | –   | ns   |
| Rise Time                                           |                                                                                                                                    | t <sub>r</sub>      | –   | 7     | –   |      |
| Turn-off Delay Time                                 |                                                                                                                                    | t <sub>d(off)</sub> | –   | 46.5  | –   |      |
| Fall Time                                           |                                                                                                                                    | t <sub>f</sub>      | –   | 15.3  | –   |      |
| Turn-on Switching Loss per Pulse                    |                                                                                                                                    | E <sub>on</sub>     | –   | 216   | –   | μJ   |
| Turn-off Switching Loss per Pulse                   |                                                                                                                                    | E <sub>off</sub>    | –   | 108.5 | –   |      |
| Input Capacitance                                   | V <sub>DS</sub> = 800 V, V <sub>GS</sub> = 0 V, f = 1 MHz                                                                          | C <sub>ies</sub>    | –   | 3227  | –   | pF   |
| Output Capacitance                                  |                                                                                                                                    | C <sub>oes</sub>    | –   | 829   | –   |      |
| Reverse Transfer Capacitance                        |                                                                                                                                    | C <sub>res</sub>    | –   | 19    | –   |      |
| Total Gate Charge                                   | V <sub>DS</sub> = 600 V, I <sub>D</sub> = 20 A,<br>V <sub>GS</sub> = 20 V                                                          | Q <sub>g</sub>      | –   | 112   | –   | nC   |
| Thermal Resistance – chip-to-<br>heatsink           | Thermal grease,<br>Thickness = 2 Mil ±2%<br>λ = 2.87 W/mK                                                                          | R <sub>thJH</sub>   | –   | 0.88  | –   | K/W  |
| Thermal Resistance – chip-to-case                   |                                                                                                                                    | R <sub>thJC</sub>   | –   | 0.61  | –   | K/W  |

## BOOST DIODE CHARACTERISTICS (D11, D21, D31)

|                                       |                                                                                                                                    |                  |     |       |     |      |
|---------------------------------------|------------------------------------------------------------------------------------------------------------------------------------|------------------|-----|-------|-----|------|
| Diode Reverse Leakage Current         | V <sub>R</sub> = 1200 V                                                                                                            | I <sub>R</sub>   | –   | –     | 400 | μA   |
| Diode Forward Voltage                 | I <sub>F</sub> = 40 A, T <sub>J</sub> = 25°C                                                                                       | V <sub>F</sub>   | 1.2 | 1.57  | 1.9 | V    |
|                                       | I <sub>F</sub> = 40 A, T <sub>J</sub> = 175°C                                                                                      |                  | –   | –     | –   |      |
| Reverse Recovery Time                 | T <sub>J</sub> = 25°C<br>V <sub>DS</sub> = 700 V, V <sub>GS</sub> = –5 V to 20 V<br>I <sub>D</sub> = 40 A, R <sub>G</sub> = 4.7 Ω  | t <sub>rr</sub>  | –   | 16.7  | –   | ns   |
| Reverse Recovery Charge               |                                                                                                                                    | Q <sub>rr</sub>  | –   | 329.6 | –   | nC   |
| Peak Reverse Recovery Current         |                                                                                                                                    | I <sub>RRM</sub> | –   | 34.3  | –   | A    |
| Peak Rate of Fall of Recovery Current |                                                                                                                                    | di/dt            | –   | 6684  | –   | A/μs |
| Reverse Recovery Energy               |                                                                                                                                    | E <sub>rr</sub>  | –   | 176.6 | –   | μJ   |
| Reverse Recovery Time                 | T <sub>J</sub> = 125°C<br>V <sub>DS</sub> = 700 V, V <sub>GS</sub> = –5 V to 20 V<br>I <sub>D</sub> = 40 A, R <sub>G</sub> = 4.7 Ω | t <sub>rr</sub>  | –   | 16.9  | –   | ns   |
| Reverse Recovery Charge               |                                                                                                                                    | Q <sub>rr</sub>  | –   | 361   | –   | nC   |
| Peak Reverse Recovery Current         |                                                                                                                                    | I <sub>RRM</sub> | –   | 37    | –   | A    |
| Peak Rate of Fall of Recovery Current |                                                                                                                                    | di/dt            | –   | 8067  | –   | A/μs |
| Reverse Recovery Energy               |                                                                                                                                    | E <sub>rr</sub>  | –   | 209.1 | –   | μJ   |

# NXH40B120MNQ1SNG

## ELECTRICAL CHARACTERISTICS (T<sub>J</sub> = 25°C unless otherwise specified) (continued)

| Characteristic | Test Conditions | Symbol | Min | Typ | Max | Unit |
|----------------|-----------------|--------|-----|-----|-----|------|
|----------------|-----------------|--------|-----|-----|-----|------|

### BOOST DIODE CHARACTERISTICS (D11, D21, D31)

|                                       |                                       |                  |   |      |   |     |
|---------------------------------------|---------------------------------------|------------------|---|------|---|-----|
| Thermal Resistance – chip-to-heatsink | Thermal grease, Thickness = 2 Mil ±2% | R <sub>θJH</sub> | – | 0.87 | – | K/W |
| Thermal Resistance – chip-to-case     | λ = 2.87 W/mK                         | R <sub>θJC</sub> | – | 0.62 | – | K/W |

### BYPASS DIODE CHARACTERISTICS (D12, D22, D32)

|                                       |                                                |                  |     |      |     |      |
|---------------------------------------|------------------------------------------------|------------------|-----|------|-----|------|
| Diode Reverse Leakage Current         | V <sub>R</sub> = 1200 V, T <sub>J</sub> = 25°C | I <sub>R</sub>   | –   | –    | 250 | μA   |
| Diode Forward Voltage                 | I <sub>F</sub> = 50 A, T <sub>J</sub> = 25°C   | V <sub>F</sub>   | 0.8 | 1.13 | 1.3 | V    |
|                                       | I <sub>F</sub> = 50 A, T <sub>J</sub> = 150°C  |                  | –   | –    | –   |      |
| Thermal Resistance – chip-to-heatsink | Thermal grease, Thickness = 2 Mil ±2%          | R <sub>θJH</sub> | –   | 1.05 | –   | °C/W |
| Thermal Resistance – chip-to-case     | λ = 2.87 W/mK                                  | R <sub>θJC</sub> | –   | 0.72 | –   | °C/W |

### THERMISTOR CHARACTERISTICS

|                            |                          |                  |    |      |   |      |
|----------------------------|--------------------------|------------------|----|------|---|------|
| Nominal resistance         |                          | R <sub>25</sub>  | –  | 22   | – | kΩ   |
| Nominal resistance         | T = 100°C                | R <sub>100</sub> | –  | 1468 | – | Ω    |
| Deviation of R25           |                          | ΔR/R             | –5 | –    | 5 | %    |
| Power dissipation          |                          | P <sub>D</sub>   | –  | 200  | – | mW   |
| Power dissipation constant |                          |                  | –  | 2    | – | mW/K |
| B-value                    | B(25/50), tolerance ±3%  |                  | –  | 3950 | – | K    |
| B-value                    | B(25/100), tolerance ±3% |                  | –  | 3998 | – | K    |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

## ORDERING INFORMATION

| Part Number      | Marking          | Package                                                       | Shipping                |
|------------------|------------------|---------------------------------------------------------------|-------------------------|
| NXH40B120MNQ1SNG | NXH40B120MNQ1SNG | Q1 3-Channel BOOST – Case 180BQ<br>Solder Pins<br>(Pb – Free) | 21 Units / Blister Tray |

## TYPICAL CHARACTERISTICS – MOSFET, BOOST DIODE AND BYPASS DIODE

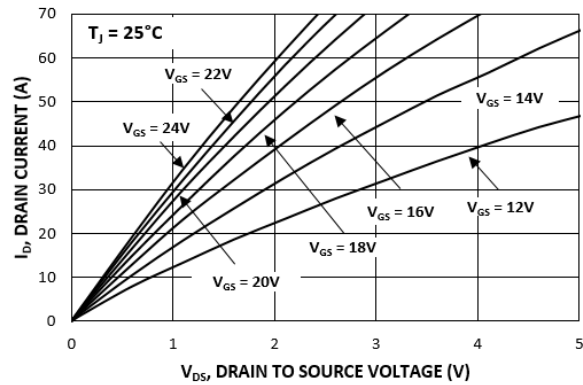


Figure 2. Typical Output Characteristics

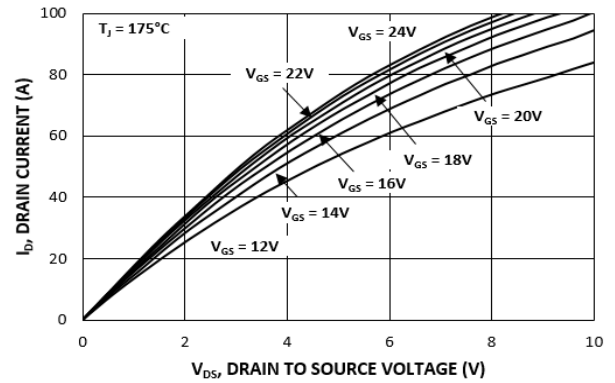


Figure 3. Typical Output Characteristics

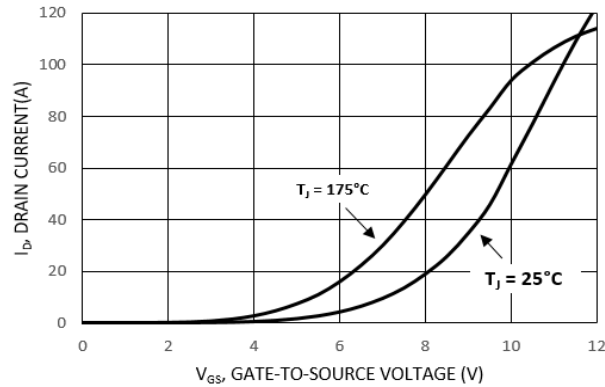


Figure 4. Typical Transfer Characteristics

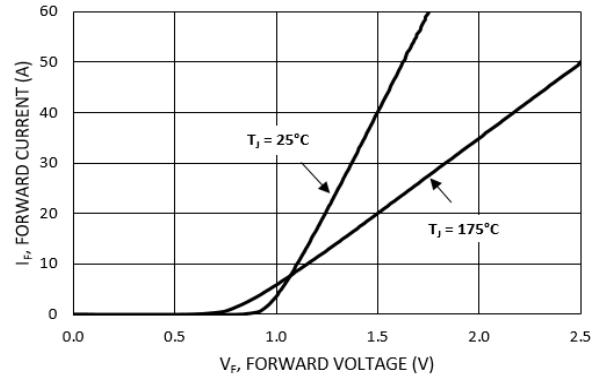


Figure 5. Boost Diode Forward Characteristics

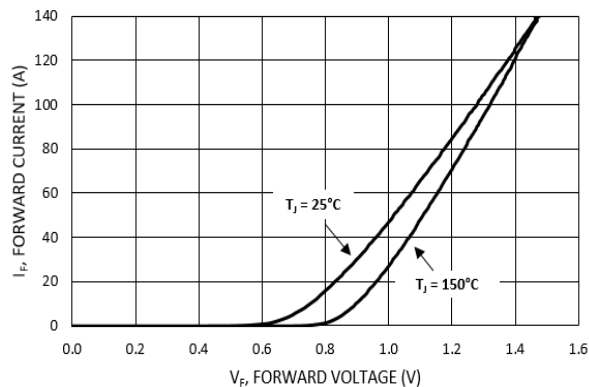


Figure 6. BYPASS Diode Forward Characteristics

# NXH40B120MNQ1SNG

## TYPICAL CHARACTERISTICS –MOSFET, BOOST DIODE AND BYPASS DIODE

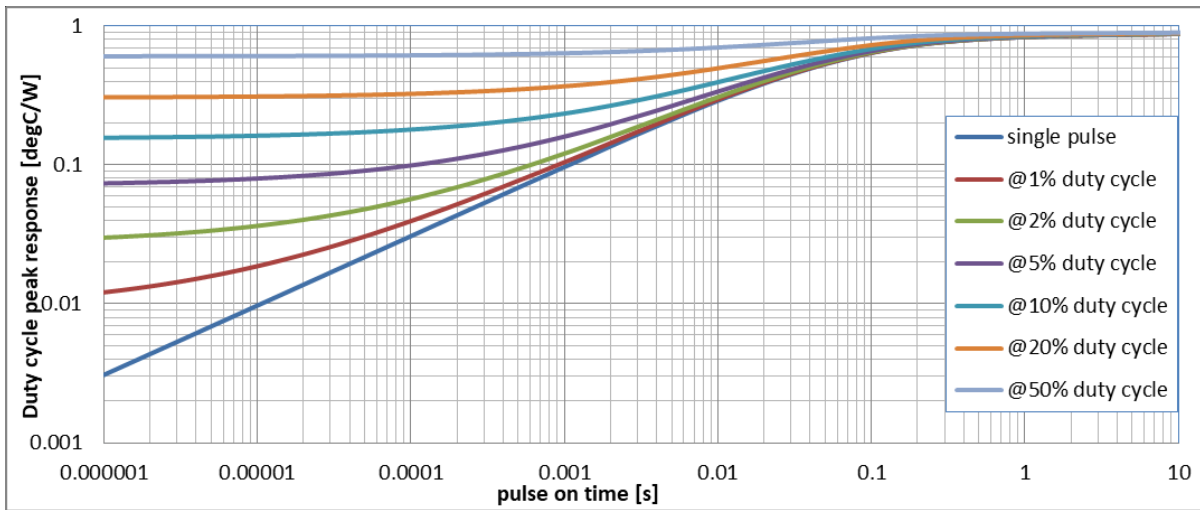


Figure 7. Transient Thermal Impedance (MOSFET)

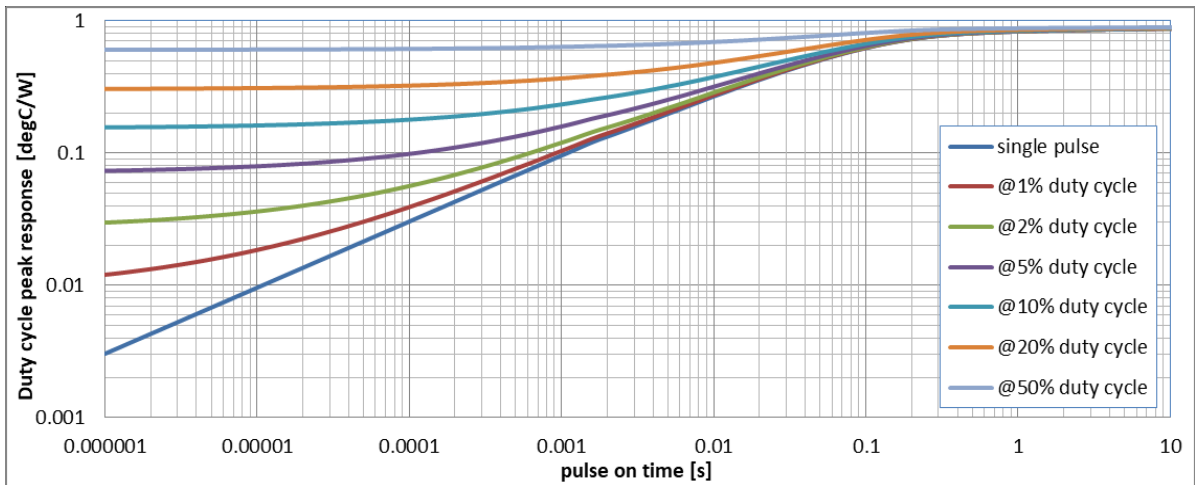


Figure 8. Transient Thermal Impedance (BOOST DIODE)

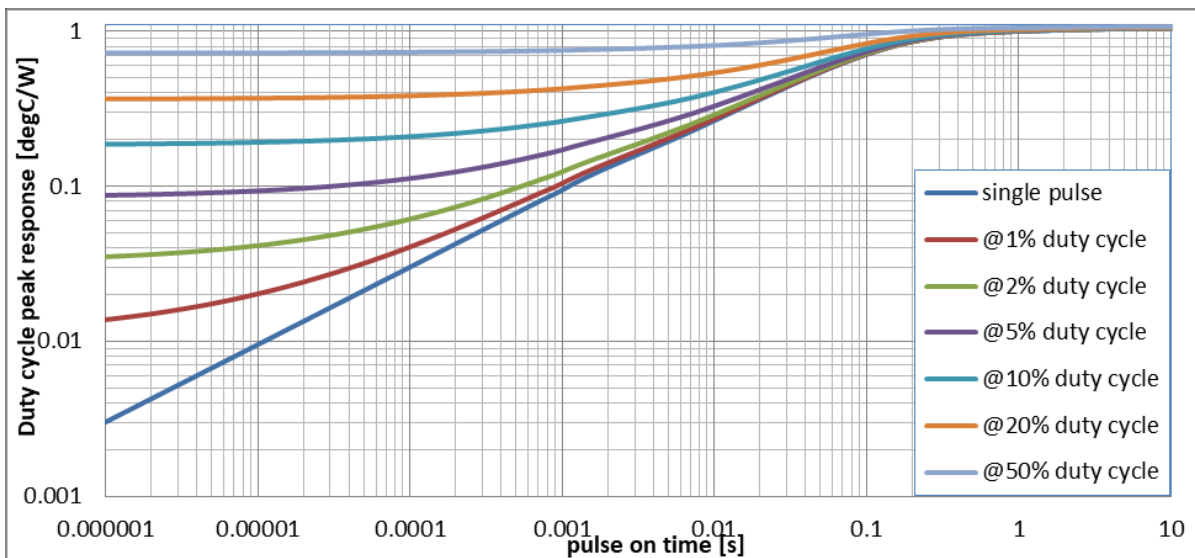


Figure 9. Transient Thermal Impedance (BYPASS DIODE)

# NXH40B120MNQ1SNG

## TYPICAL CHARACTERISTICS – MOSFET, BOOST DIODE AND BYPASS DIODE

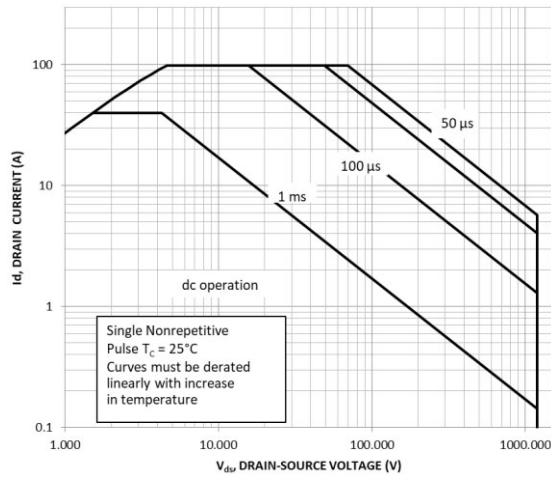


Figure 10. FBSOA

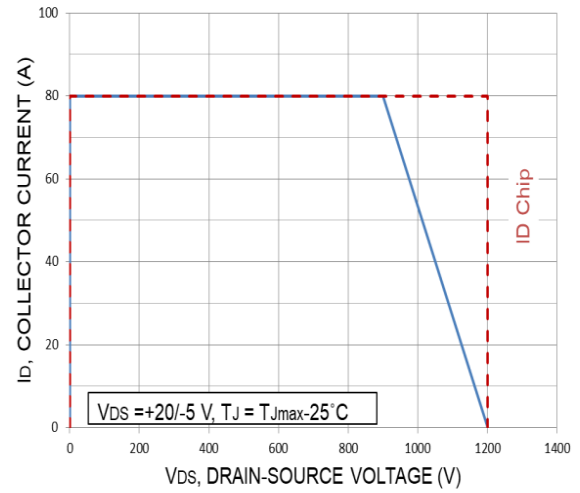


Figure 11. RBSOA

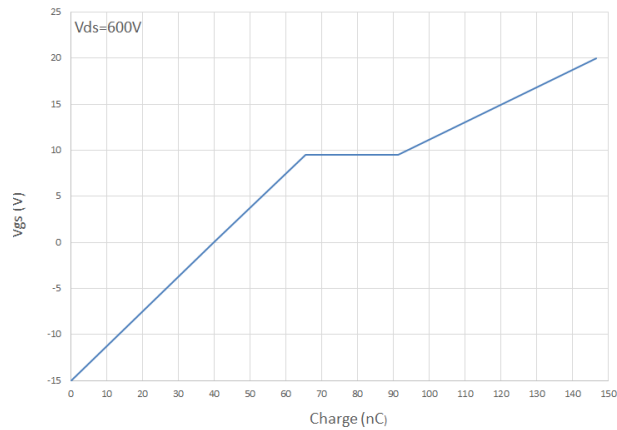


Figure 12. Gate Voltage vs. Gate Charge

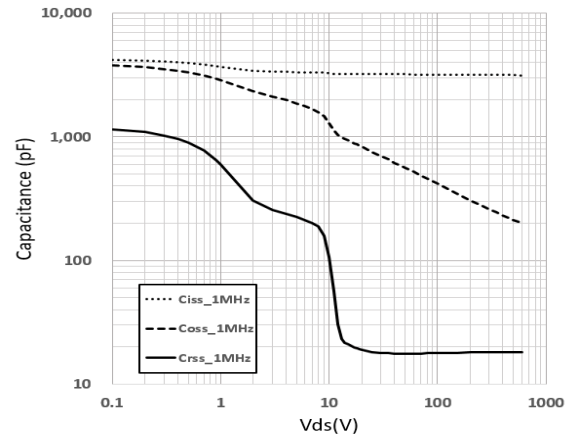


Figure 13. Capacitance Charge

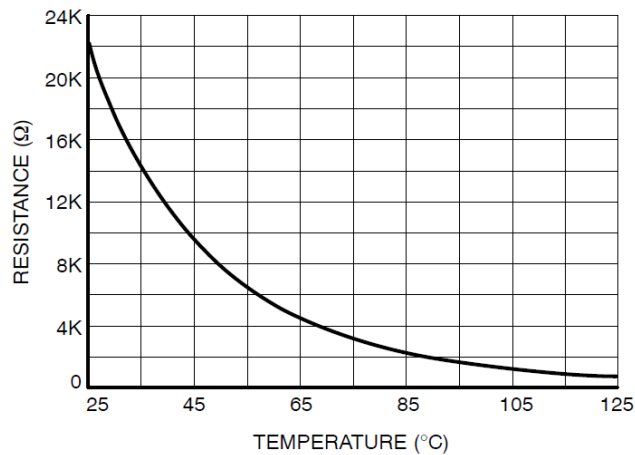


Figure 14. Thermistor Characteristics

# NXH40B120MNQ1SNG

## TYPICAL CHARACTERISTICS – MOSFET (M11, M21, M31) AND BOOST DIODE (D11, D21, D31)

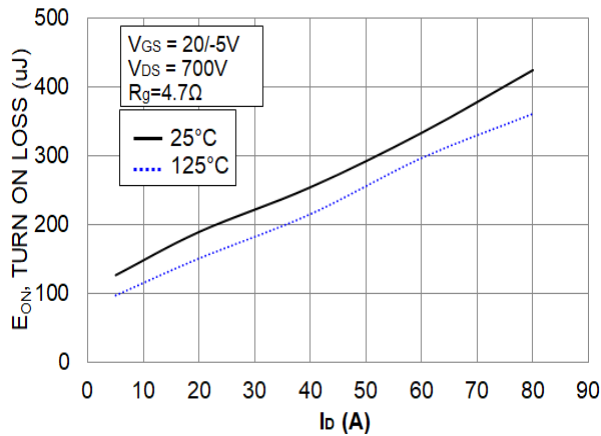


Figure 15. Typical Turn ON Loss vs.  $I_D$

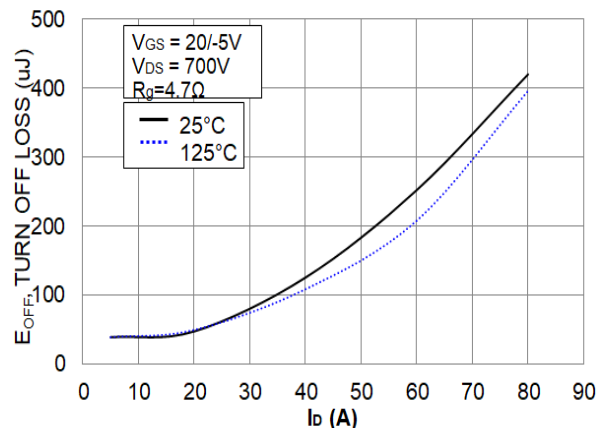


Figure 16. Typical Turn OFF Loss vs.  $I_D$

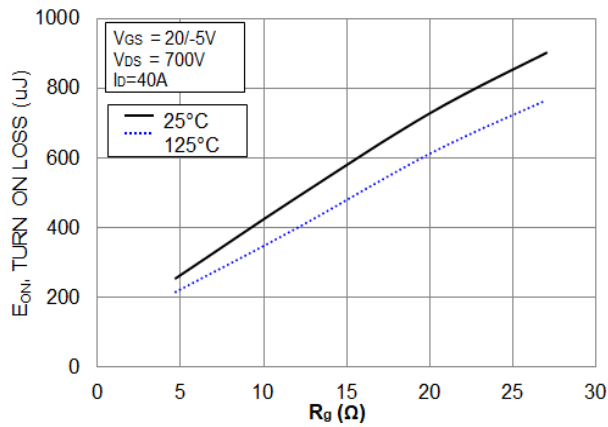


Figure 17. Typical Turn ON Loss vs.  $R_g$

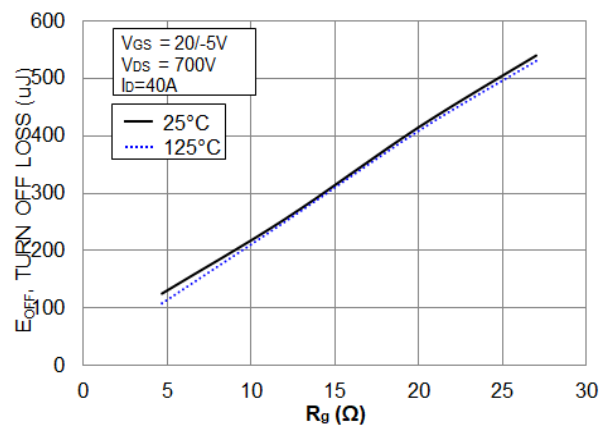


Figure 18. Typical Turn OFF Loss vs.  $R_g$

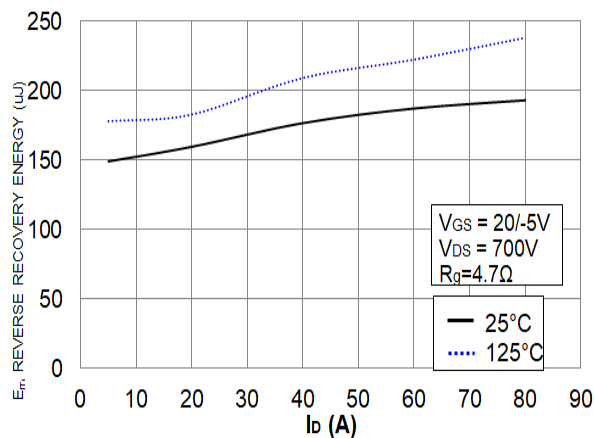


Figure 19. Typical Reverse Recovery Energy Loss vs.  $I_D$

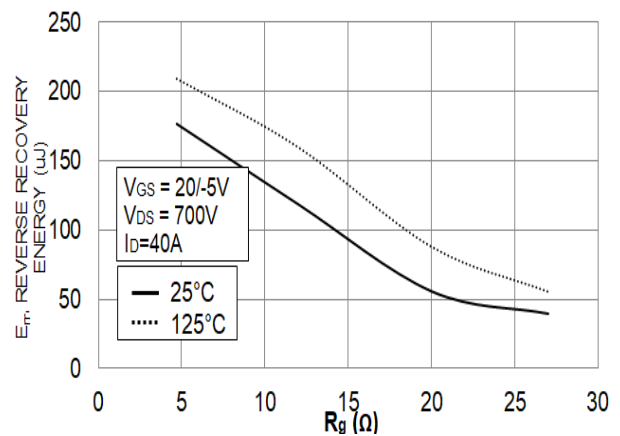


Figure 20. Typical Reverse Recovery Energy Loss vs.  $R_g$

# NXH40B120MNQ1SNG

## TYPICAL CHARACTERISTICS – MOSFET (M11, M21 ,M31) AND BOOST DIODE (D11, D21, D31) (continued)

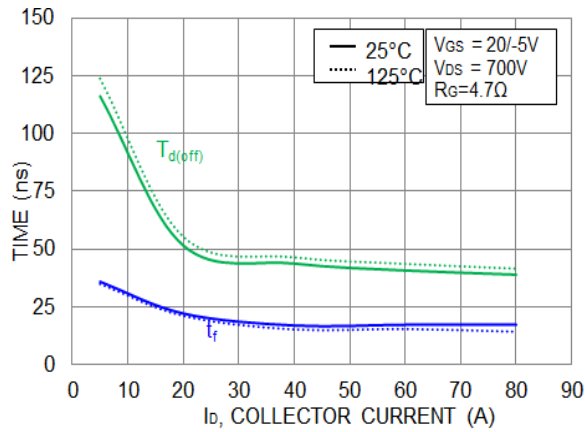


Figure 21. Typical Turn-Off Switching Time vs.  $I_D$

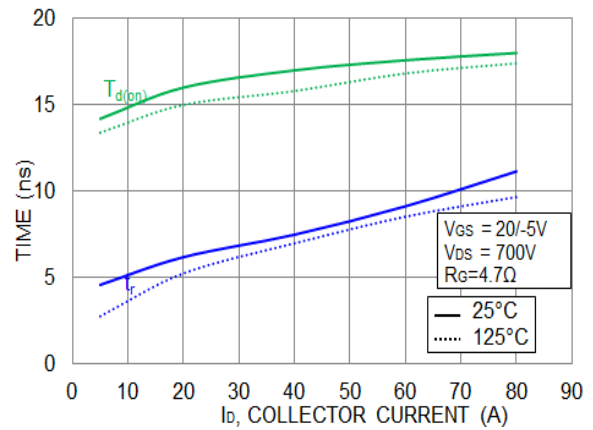


Figure 22. Typical Turn-On Switching Time vs.  $I_D$

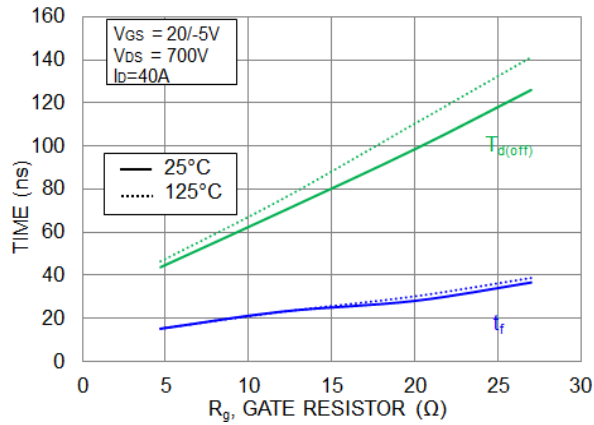


Figure 23. Typical Turn-Off Switching Time vs.  $R_G$

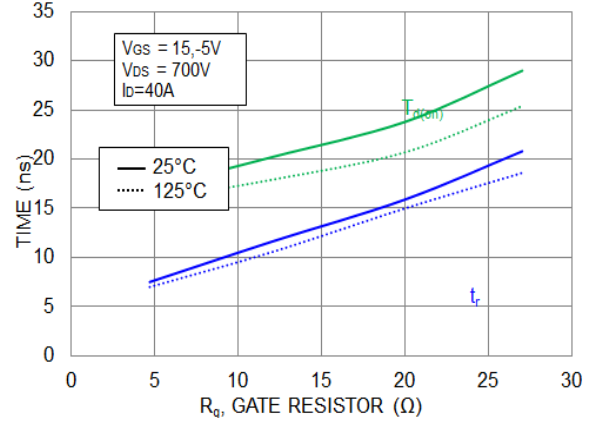


Figure 24. Typical Turn-On Switching Time vs.  $R_G$

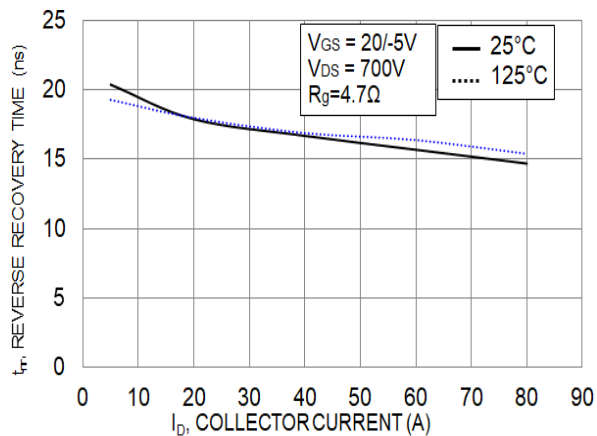


Figure 25. Inverse Diode  
Typical Reverse Recovery Time vs.  $I_D$

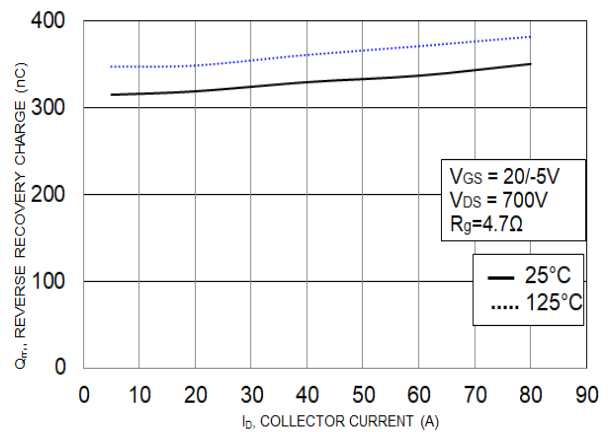


Figure 26. Typical Reverse Recovery Charge vs.  $I_D$

# NXH40B120MNQ1SNG

## TYPICAL CHARACTERISTICS – MOSFET (M11, M21, M31) AND BOOST DIODE (D11, D21, D31) (continued)

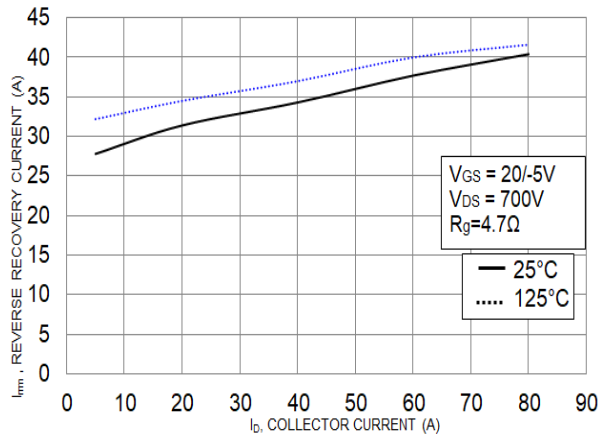


**Figure 27. Inverse Diode  
Typical Reverse Recovery Current vs.  $I_D$**

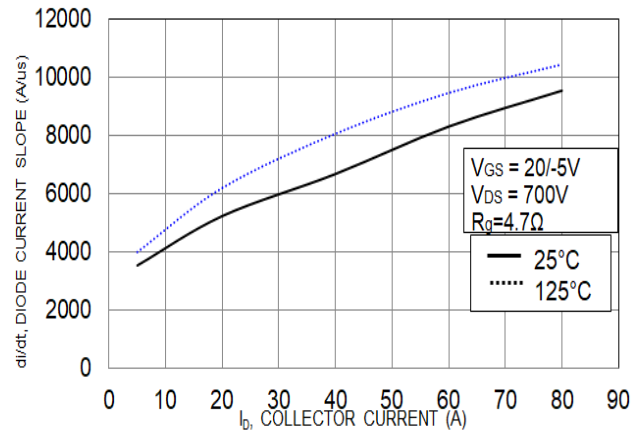


**Figure 28. Typical di/dt Current Slope  
versus  $I_D$**

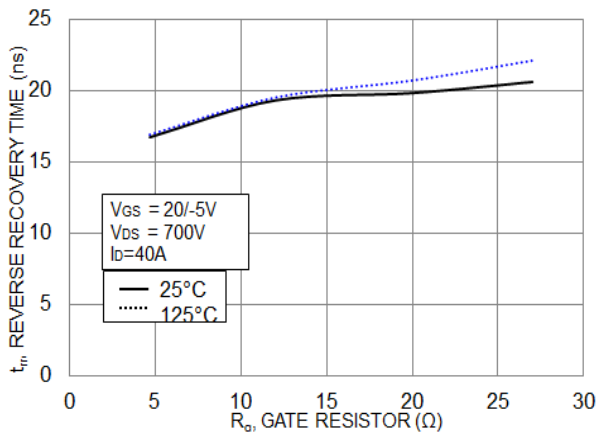


**Figure 29. Typical Reverse Recovery Time vs.  $R_G$**

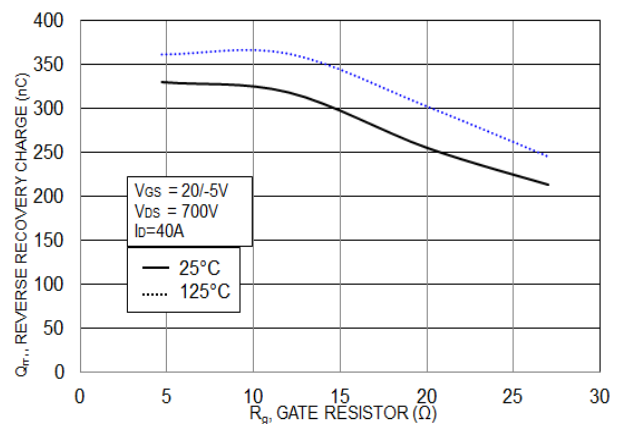


**Figure 30. Inverse Diode  
Typical Reverse Recovery Charge vs.  $R_G$**

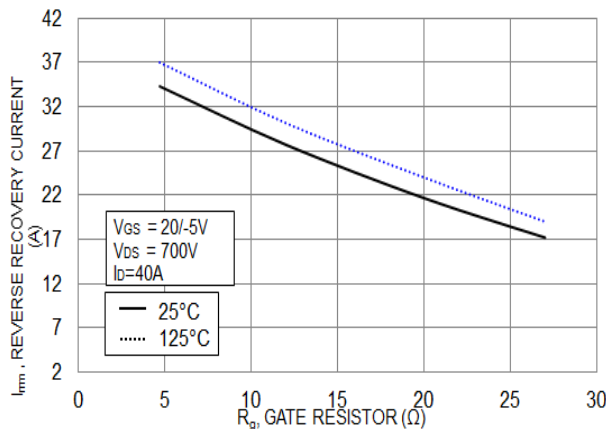


**Figure 31. Typical Reverse Recovery Peak Current  
versus  $R_G$**

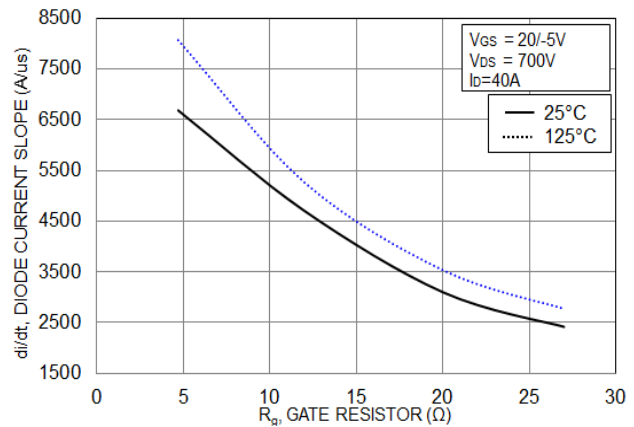
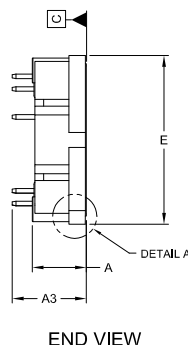
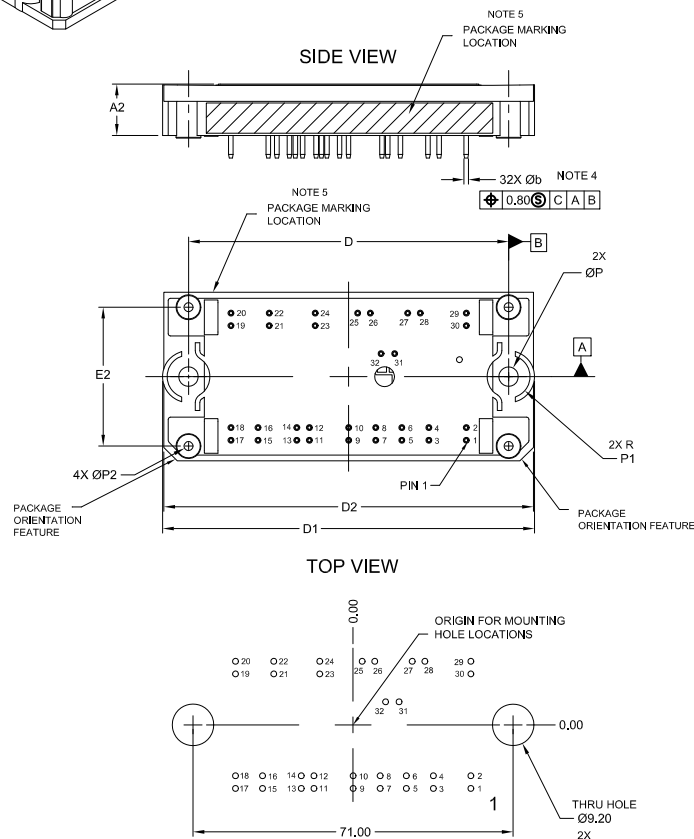
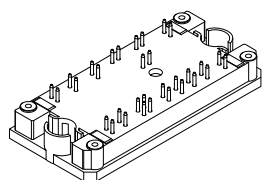


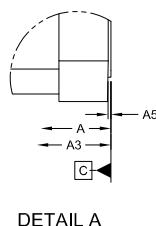
**Figure 32. Inverse Diode Typical di/dt vs.  $R_G$**

**PIM32, 71x37.4 (SOLDER PIN)**  
CASE 180BQ  
ISSUE A

DATE 23 JUL 2021



| DIM | MILLIMETERS |          |       |
|-----|-------------|----------|-------|
|     | MIN.        | NOM.     | MAX.  |
| A   | 11.70       | 12.00    | 12.30 |
| A2  | 10.90       | 11.40    | 11.90 |
| A3  | 15.90       | 16.40    | 16.90 |
| A5  | 0.00        | -        | 0.45  |
| b   | 0.90        | 1.00     | 1.10  |
| D   | 70.50       | 71.00    | 71.50 |
| D1  | 82.00       | 82.50    | 83.00 |
| D2  | 81.50       | 82.00    | 82.50 |
| E   | 36.90       | 37.40    | 37.90 |
| E2  | 30.30       | 30.80    | 31.30 |
| P   | 4.30        | 4.40     | 4.50  |
| P1  | 4.55        | 4.75     | 4.95  |
| P2  |             | 2.00 REF |       |

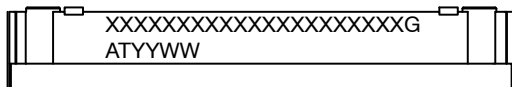


| NOTE 4 |              |        |     |              |        |
|--------|--------------|--------|-----|--------------|--------|
| PIN    | PIN POSITION |        | PIN | PIN POSITION |        |
|        | X            | Y      |     | X            | Y      |
| 1      | 26,10        | -14,10 | 17  | -26,10       | -14,10 |
| 2      | 26,10        | -11,30 | 18  | -26,10       | -11,30 |
| 3      | 17,80        | -14,10 | 19  | -26,10       | 11,30  |
| 4      | 17,80        | -11,30 | 20  | -26,10       | 14,10  |
| 5      | 11,80        | -14,10 | 21  | -17,60       | 11,30  |
| 6      | 11,80        | -11,30 | 22  | -17,60       | 14,10  |
| 7      | 6,00         | -14,10 | 23  | -7,40        | 11,30  |
| 8      | 6,00         | -11,30 | 24  | -7,40        | 14,10  |
| 9      | 0,00         | -14,10 | 25  | 2,00         | 14,10  |
| 10     | 0,00         | -11,30 | 26  | 4,80         | 14,10  |
| 11     | -8,70        | -14,10 | 27  | 13,10        | 14,10  |
| 12     | -8,70        | -11,30 | 28  | 15,90        | 14,10  |
| 13     | -11,50       | -14,10 | 29  | 26,10        | 14,10  |
| 14     | -11,50       | -11,30 | 30  | 26,10        | 11,30  |
| 15     | -20,10       | -14,10 | 31  | 10,20        | 5,10   |
| 16     | -20,10       | -11,30 | 32  | 7,20         | 5,10   |

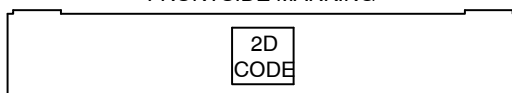
## RECOMMENDED MOUNTING PATTERN\*

For additional information on our Pb-Free strategy and soldering details, please download the On Semiconductor Soldering and Mounting Techniques Reference Manual, [SOLDERM/D](#).

### GENERIC MARKING DIAGRAM\*



## FRONTSIDE MARKING



## BACKSIDE MARKING

XXXXX = Specific Device Code  
G = Pb-Free Package  
AT = Assembly & Test Site Code  
YYWW = Year and Work Week Code

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

|                  |             |
|------------------|-------------|
| DOCUMENT NUMBER: | 98AON15094H |
|------------------|-------------|

Electronic versions are uncontrolled except when accessed directly from the Document Repository.  
Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.

|                     |                                    |
|---------------------|------------------------------------|
| <b>DESCRIPTION:</b> | <b>PIM32, 71x37.4 (SOLDER PIN)</b> |
|---------------------|------------------------------------|

PAGE 1 OF 1

**onsemi** and **onsemi** are trademarks of Semiconductor Components Industries, LLC dba **onsemi** or its subsidiaries in the United States and/or other countries. **onsemi** reserves the right to make changes without further notice to any products herein. **onsemi** makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. **onsemi** does not convey any license under its patent rights nor the rights of others.

**onsemi**, **Onsemi**, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at [www.onsemi.com/site/pdf/Patent-Marking.pdf](http://www.onsemi.com/site/pdf/Patent-Marking.pdf). **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

## ADDITIONAL INFORMATION

### TECHNICAL PUBLICATIONS:

Technical Library: [www.onsemi.com/design/resources/technical-documentation](http://www.onsemi.com/design/resources/technical-documentation)  
onsemi Website: [www.onsemi.com](http://www.onsemi.com)

### ONLINE SUPPORT: [www.onsemi.com/support](http://www.onsemi.com/support)

For additional information, please contact your local Sales Representative at  
[www.onsemi.com/support/sales](http://www.onsemi.com/support/sales)